

# Supplementary Information for: “Valence mediated tunable magnetism and electronic properties by ferroelectric polarization switching in 2D FeI<sub>2</sub>/In<sub>2</sub>Se<sub>3</sub> van der Waals heterostructures”

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## Part I. Relative energy of 6 different interface contact types

For the FeI<sub>2</sub>/In<sub>2</sub>Se<sub>3</sub> van der Waals heterostructure (HS), we constructed six different interfacial contact types and fully released the lattice constant in the *xy*-plane and spatial ion coordinates, as shown in Fig. S1. These types of relative energy ( $\Delta E$ ) and interfacial adsorption energy were calculated to confirm the most stable combination among them, as shown in Table S1. The interface adsorption energy of all structures that defined as  $E_{ad} = (E_{FeI_2/In_2Se_3} - E_{FeI_2} - E_{In_2Se_3})/A$ , where the  $E_{FeI_2/In_2Se_3}$  is the total energy of the HS,  $E_{FeI_2}$  and  $E_{In_2Se_3}$  represent the energy of the FeI<sub>2</sub> and In<sub>2</sub>Se<sub>3</sub> parts with the same supercell constant, respectively. In addition, the area of interface in the HS is indicated by *A*. The physical meaning of the equation is that the energy released by combining the FeI<sub>2</sub> and In<sub>2</sub>Se<sub>3</sub> part into a HS, which can describe the thermodynamic stability of the interface. Therefore, we calculated the interface adsorption energy, which ranges from −0.037 to −0.035 eV/Å<sup>2</sup>. These negative values show that all structures are stable. By comparing the

relative energies, we finally determined that type-4 was the most stable structure applied in the calculations below.

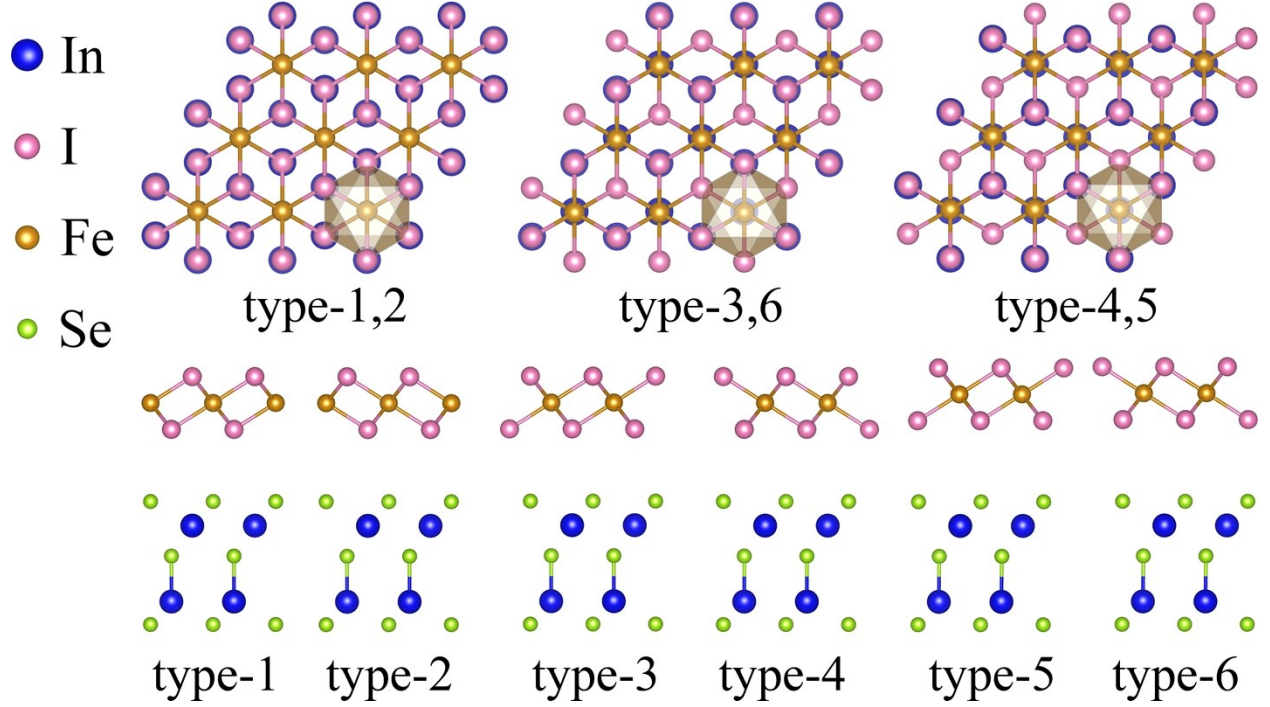


Fig. S1. Top view and side view of six different interfacial contact types for the  $\text{FeI}_2/\text{In}_2\text{Se}_3$  HS. The type- $m,n$  represents the top view of the type- $m$  and the type- $n$ .

Table S1. The relative energy ( $\Delta E$ , in eV) and interfacial adsorption energy ( $E_{\text{ad}}$ , in eV/Å<sup>2</sup>) of six different interfacial contact types for the  $\text{FeI}_2/\text{In}_2\text{Se}_3$  HS.

	type-1	type-2	type-3	type-4	type-5	type-6
$\Delta E$	0.018	0.018	0.002	0.000	0.097	0.082
$E_{\text{ad}}$	-0.037	-0.037	-0.037	-0.037	-0.035	-0.036

## Part II. The layer-resolved partial DOS of the $\text{FeI}_2/\text{bilayer In}_2\text{Se}_3$ HS

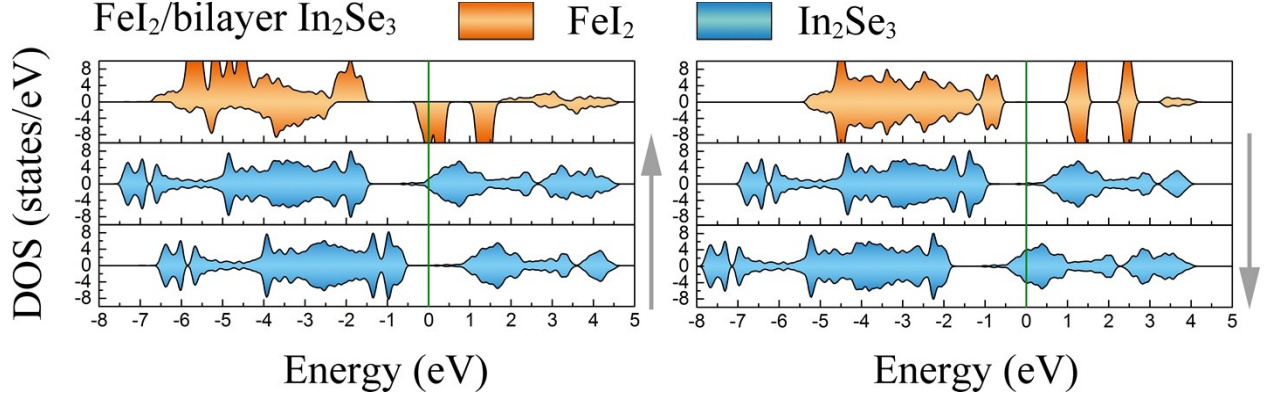


Fig. S2. The layer-resolved partial DOS of the  $\text{FeI}_2/\text{bilayer In}_2\text{Se}_3$  HS. The gray arrow represents the direction of polarization.

### Part III. The layer-resolved partial DOS of the $\text{MnI}_2/\text{In}_2\text{Se}_3$ and $\text{CoI}_2/\text{In}_2\text{Se}_3$ HS

We also calculated  $\text{MnI}_2/\text{In}_2\text{Se}_3$  HS and  $\text{CoI}_2/\text{In}_2\text{Se}_3$  HS, and their layer-resolved partial DOS is shown in Fig. S3. We found that they have the same conclusion as  $\text{FeI}_2/\text{In}_2\text{Se}_3$  HS, that is, in the  $+P$  case, the HS exhibits Ferromagnetic ordering, when it reverses to  $-P$  case, the magnetic ordering changes from Ferromagnetic to antiferromagnetic ordering.

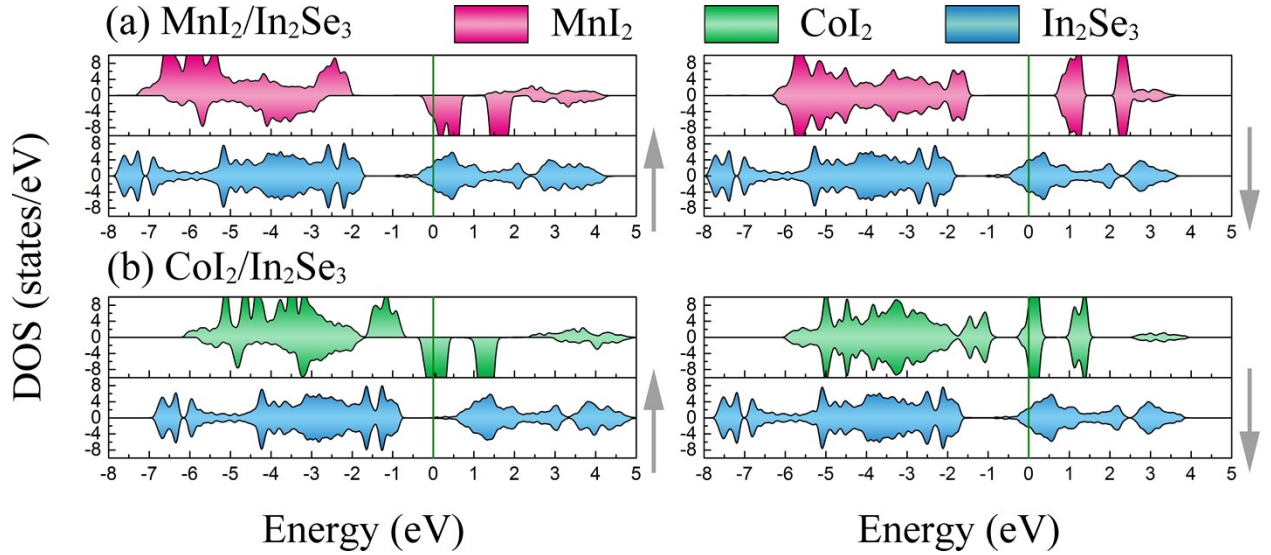


Fig. S3. The layer-resolved partial DOS of the  $\text{MnI}_2/\text{In}_2\text{Se}_3$  and  $\text{CoI}_2/\text{In}_2\text{Se}_3$  HS. The gray arrow represents the direction of polarization.